

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

- 5 Claim 1 (currently amended): A bipolar junction transistor, comprising:
a substrate;
at least a deep isolation trench formed in the substrate and at least a channel stop
region formed in the bottom of the deep isolation trench;
a dielectric layer formed on the substrate;
10 an opening formed in the dielectric layer to expose a portion of the substrate;
a selective implant collector region formed in the substrate and beneath the opening;
a heavily doped polysilicon layer formed on a sidewall of the opening to define a self-aligned base region in the opening;
an intrinsic base doped region positioned in a bottom of the opening and within the
15 self-aligned base region defined by the heavily doped polysilicon layer;
a spacer formed on the heavily doped polysilicon layer to define a self-aligned emitter region in the opening; and
an emitter conductivity layer being filled within the self-aligned emitter region, and
a PN junction being formed between the emitter conductivity layer and the intrinsic base
20 doped region.
- Claim 2 (original): The bipolar junction transistor of claim 1, wherein the heavily doped polysilicon layer comprises a boron dopant with a dosage ranging from $1\text{E}19$ to $1\text{E}21$ atoms/cm².
- 25 Claim 3 (original): The bipolar junction transistor of claim 1, wherein the substrate is a silicon substrate.

Claim 4 (original): The bipolar junction transistor of claim 1, wherein the substrate is a non-selective epitaxial silicon substrate.

- 5 Claim 5 (original): The bipolar junction transistor of claim 1, further comprising a salicide layer formed on the emitter conductivity layer.

Claim 6 (canceled)

- 10 Claim 7 (original): The bipolar junction transistor of claim 1, further comprising an extended conductivity layer formed on the dielectric layer to connect to the heavily doped polysilicon layer.

- 15 Claim 8 (original): The bipolar junction transistor of claim 7, further comprising an oxide layer and a silicon nitride layer formed between the extended conductivity layer and the dielectric layer.

- Claim 9 (original): The bipolar junction transistor of claim 7, wherein the extended conductivity layer is composed of in-situ doped polysilicon.

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- Claim 10 (original): The bipolar junction transistor of claim 7, further comprising a salicide layer formed on the extended conductivity layer.

Claim 11 (canceled)

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Claim 12 (canceled)

- Claim 13 (original): The bipolar junction transistor of claim 1, wherein the intrinsic base

doped region comprises a boron dopant.

Claim 14 (previously presented): A bipolar junction transistor, comprising:

- a substrate;
- 5 at least a deep isolation trench formed in the substrate and at least a channel stop region formed in the bottom of the deep isolation trench;
- a dielectric layer formed on the substrate;
- an opening formed in the dielectric layer to expose a portion of the substrate;
- a doped polysilicon layer formed on a sidewall of the opening and on the dielectric
- 10 layer outside of the opening, the doped polysilicon layer defining a self-aligned base region in the opening;
- an intrinsic base doped region positioned in a bottom of the opening and within the self-aligned base region defined by the doped polysilicon layer;
- a spacer formed on the doped polysilicon layer to define a self-aligned emitter region
- 15 in the opening; and
- an emitter conductivity layer being filled within the self-aligned emitter region, and a PN junction being formed between the emitter conductivity layer and the intrinsic base doped region.

- 20 Claim 15 (original): The bipolar junction transistor of claim 14, wherein the doped polysilicon layer comprises a boron dopant.

- Claim 16 (original): The bipolar junction transistor of claim 14, further comprising a salicide layer formed on the emitter conductivity layer and on the portion of the doped
- 25 polysilicon layer outside of the opening.

Claim 17 (original): The bipolar junction transistor of claim 14, further comprising a selective implant collector (SIC) region formed in the substrate beneath the intrinsic base

doped region.

Claim 18 (canceled)

5 Claim 19 (canceled)

Claim 20 (original): The bipolar junction transistor of claim 14, wherein the intrinsic base doped region comprises a boron dopant.

- 10 Claim 21 (previously presented): A bipolar junction transistor, comprising:
- a substrate;
 - at least a deep isolation trench formed in the substrate and at least a channel stop region formed in the bottom of the deep isolation trench;
 - a dielectric layer formed on the substrate;
 - 15 an opening formed in the dielectric layer to expose a portion of the substrate;
 - a heavily doped polysilicon layer formed on a sidewall of the opening to define a self-aligned base region in the opening;
 - an intrinsic base doped region positioned in a bottom of the opening and within the self-aligned base region defined by the heavily doped polysilicon layer;
 - 20 a spacer formed on the heavily doped polysilicon layer to define a self-aligned emitter region in the opening; and
 - an emitter conductivity layer being filled within the self-aligned emitter region, and a PN junction being formed between the emitter conductivity layer and the intrinsic base doped region.
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